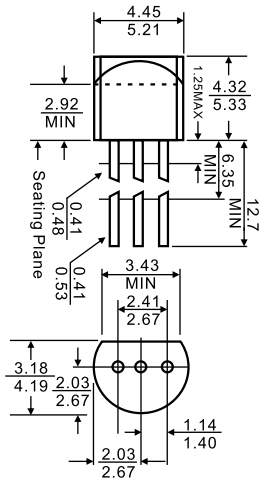
2SD1468(NPN)

TO-92 Bipolar Transistors

1. EMITTER
2. COLLECTOR
3. BASE

TO-92



Dimensions in inches and (millimeters)

Features

- ✧ Low saturation voltage
- ✧ Ideal for low voltage, high current dribes
- ✧ High DC current gain and high current

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector power dissipation	625	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50μA, I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V, I_E=0			0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V, I_C=0			0.5	μA
DC current gain	h_{FE}	V_{CE}=3V, I_C=100mA	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA			0.4	V
Transition frequency	f_T	V_{CE}=5V, I_C=50mA, f=100MHz	50			MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz			30	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560

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Typical Characteristics